

## Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 20	0.031 at $V_{GS} = - 4.5$ V	- 4.8
	0.041 at $V_{GS} = - 2.5$ V	- 4.2
	0.058 at $V_{GS} = - 1.8$ V	- 3.5

### FEATURES

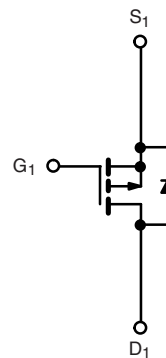
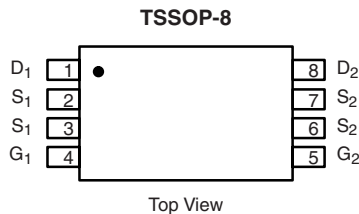
- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFETs



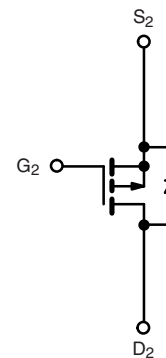
**RoHS**  
COMPLIANT

### APPLICATIONS

- Load Switch
- Battery Switch



P-Channel MOSFET



P-Channel MOSFET

Ordering Information: Si6981DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	- 20		V
Gate-Source Voltage	$V_{GS}$	$\pm 8$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	- 4.8	- 4.1
		$T_A = 70$ °C	- 3.9	- 3.2
Pulsed Drain Current (10 $\mu$ s Pulse Width)	$I_{DM}$	- 30		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	- 1.0	- 0.7	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	1.14	0.83
		$T_A = 70$ °C	0.73	0.53
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	86	110
		Steady State	124	150
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	59	75	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



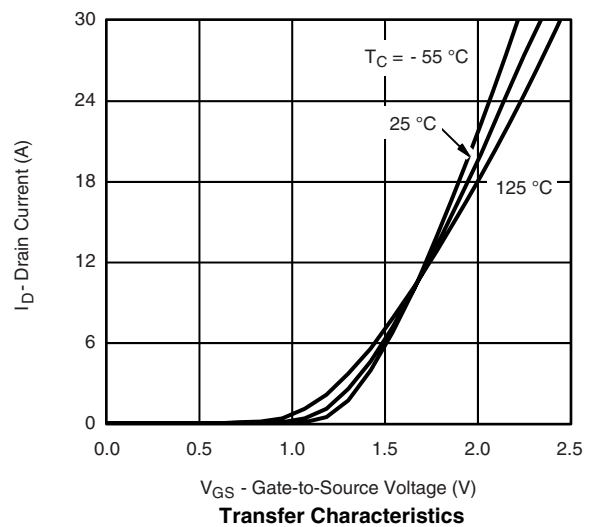
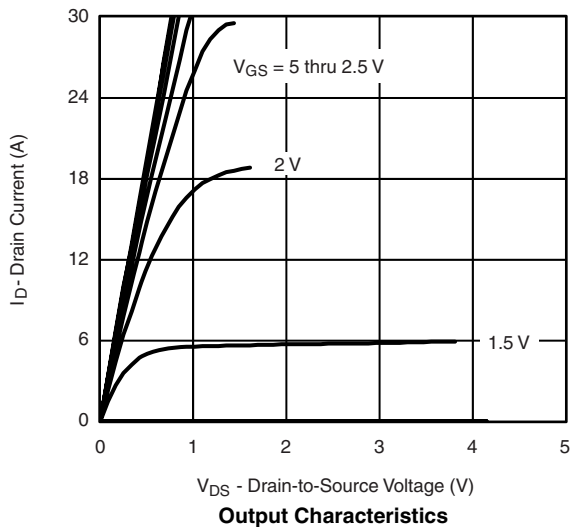
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -300\text{ }\mu\text{A}$	-0.40		-0.9	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -4.8\text{ A}$		0.026	0.031	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -4.2\text{ A}$		0.034	0.041	
		$V_{GS} = -1.8\text{ V}, I_D = -3.5\text{ A}$		0.046	0.058	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -4.8\text{ A}$		17		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.0\text{ A}, V_{GS} = 0\text{ V}$		-0.65	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4.8\text{ A}$		15	25	nC
Gate-Source Charge	$Q_{gs}$		2.4			
Gate-Drain Charge	$Q_{gd}$		3.8			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		35	55	ns
Rise Time	$t_r$		55	85		
Turn-Off Delay Time	$t_{d(off)}$		120	180		
Fall Time	$t_f$		52	80		
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	50	

Notes:

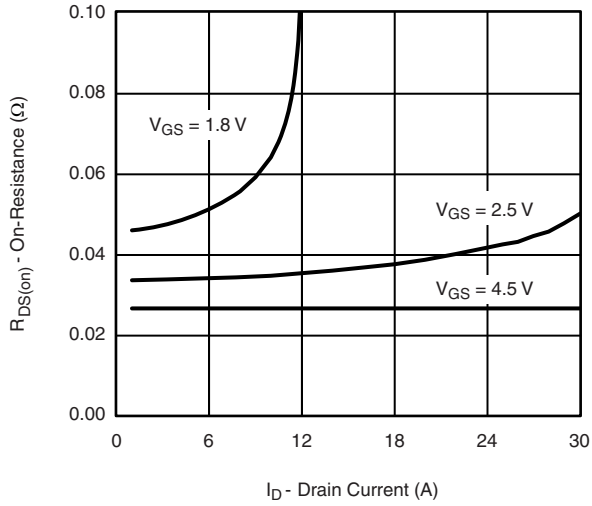
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

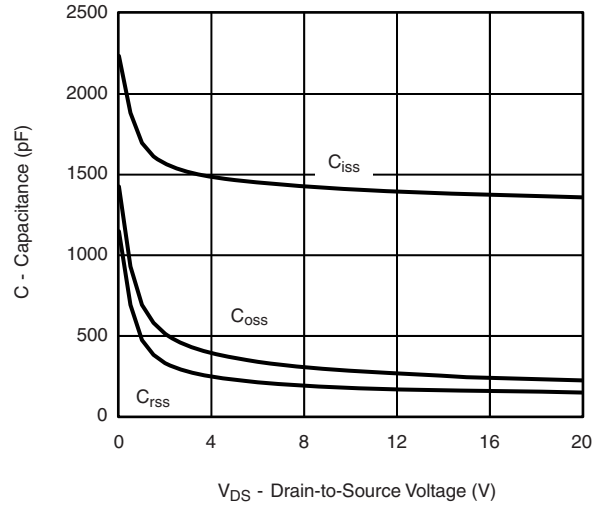
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



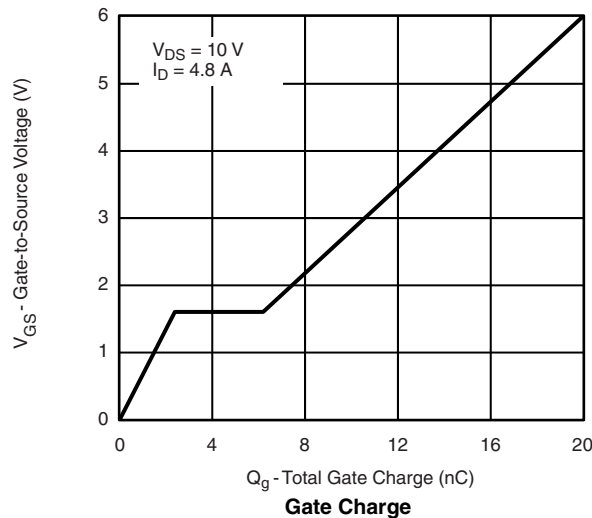
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



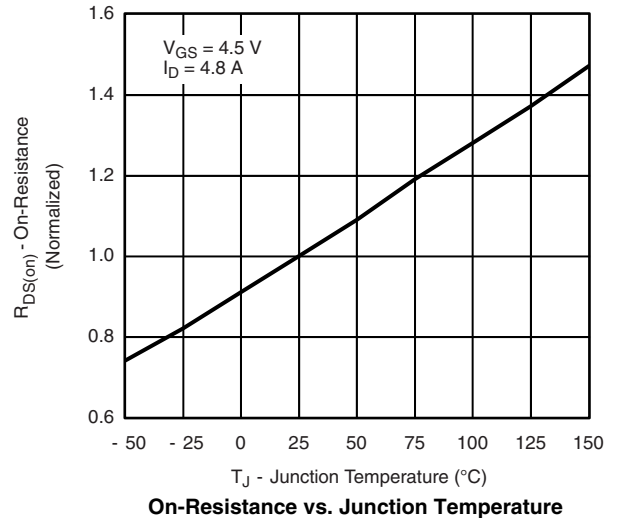
**On-Resistance vs. Drain Current**



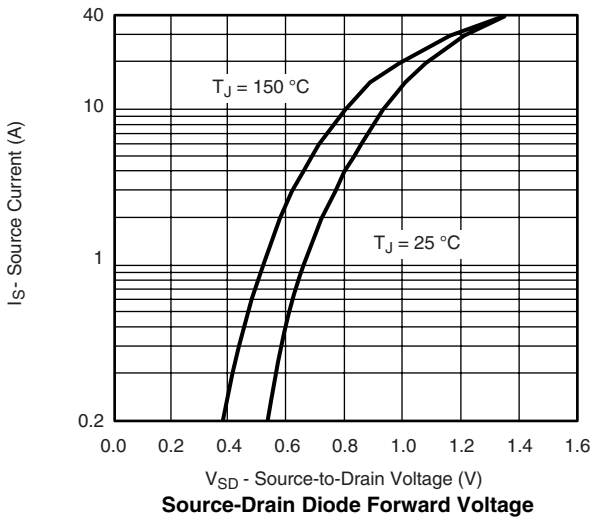
**Capacitance**



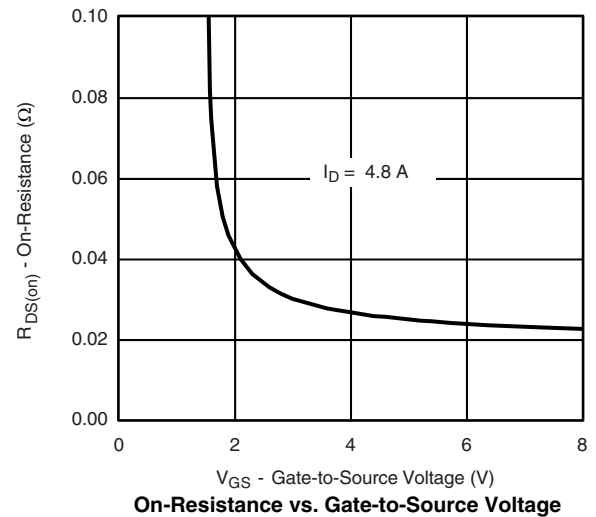
**Gate Charge**



**On-Resistance vs. Junction Temperature**

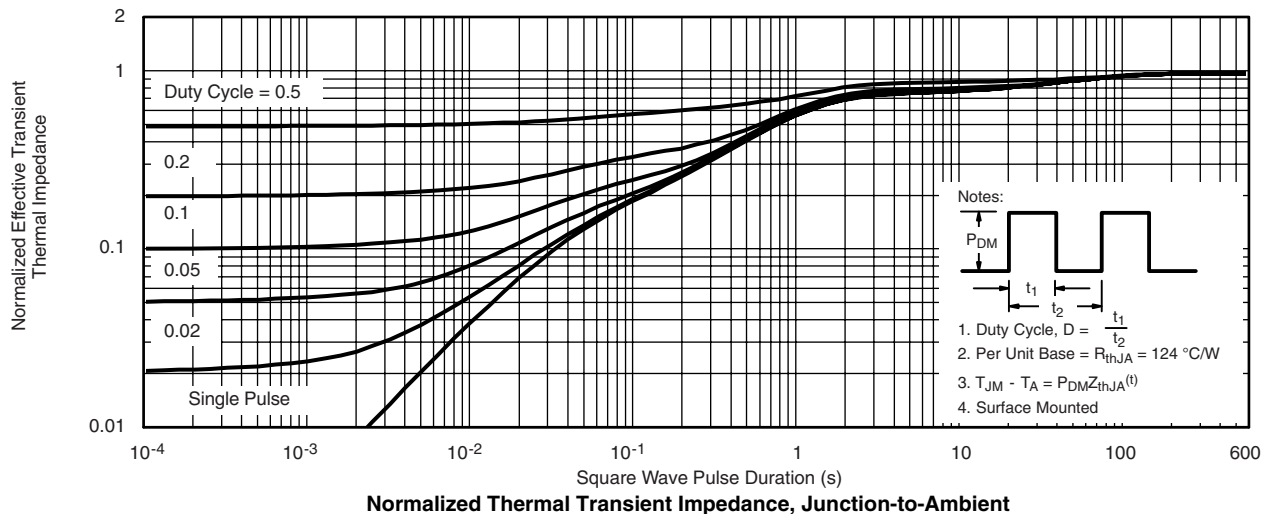
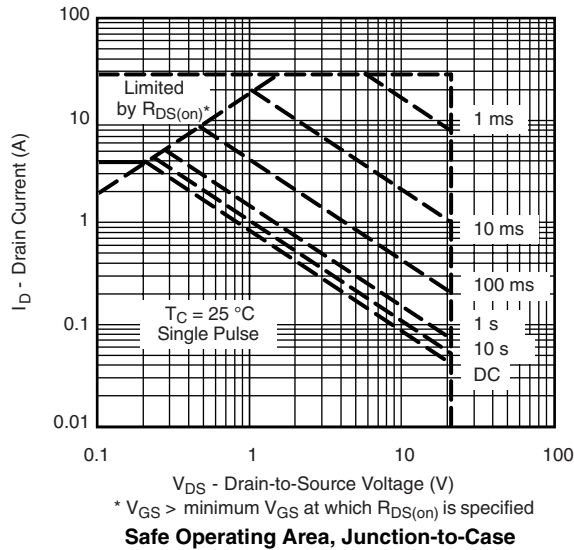
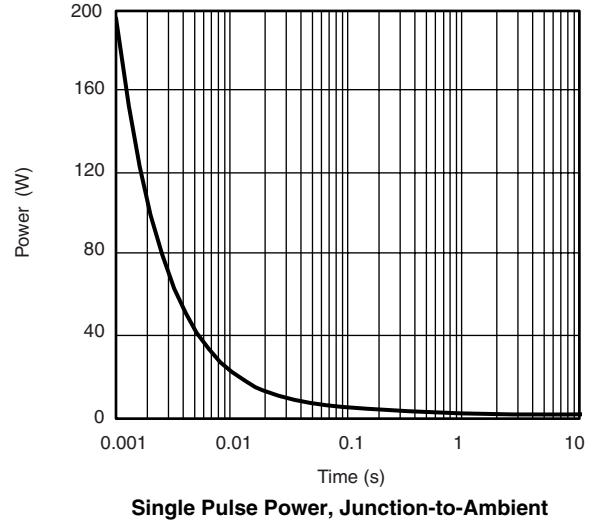
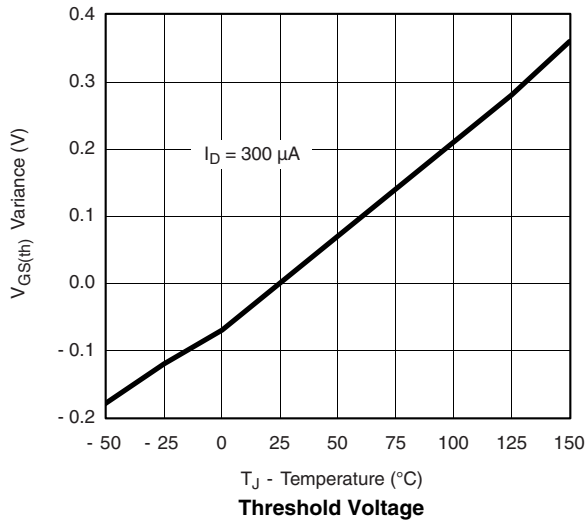


**Source-Drain Diode Forward Voltage**



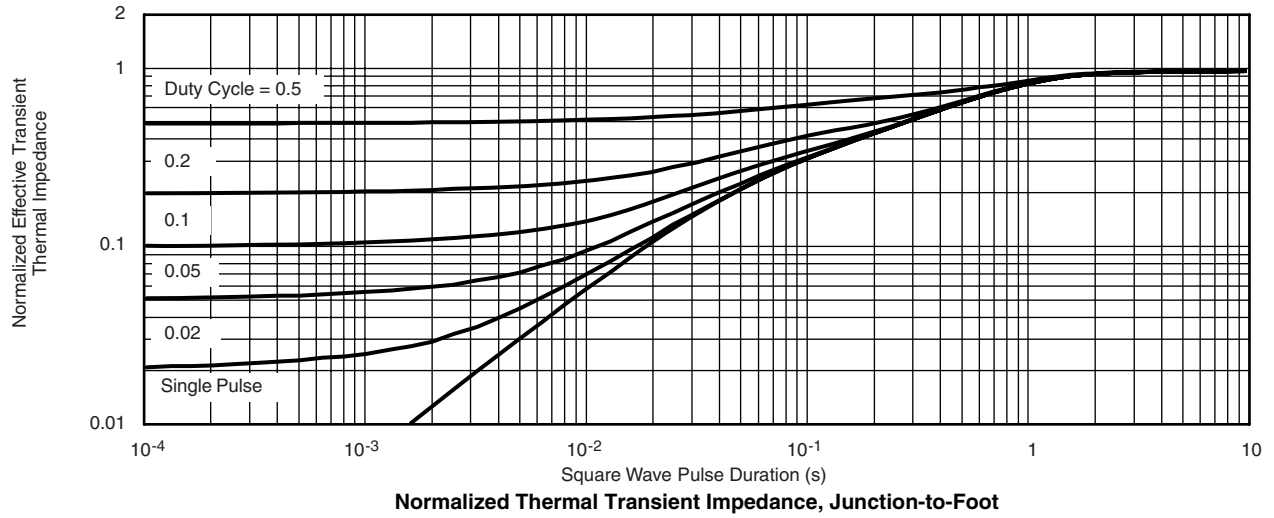
**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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